

**■Features 特点**

Low holding and latching current 低维持和擎住电流

Bidirectional switching and phase control 双向开关和相位控制

Glass passivated Process 玻璃钝化工艺

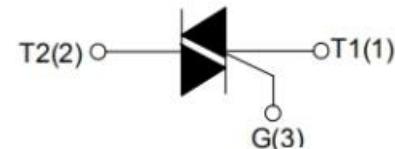
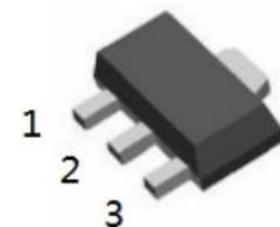
**■Applications 应用**

Microcontrollers 微控制器

Logic integrated circuits 逻辑集成电路

Low power gate trigger circuits 低功率门极触发电路

MARKING:MAC97A8

**■Absolute Maximum Ratings 最大额定值**

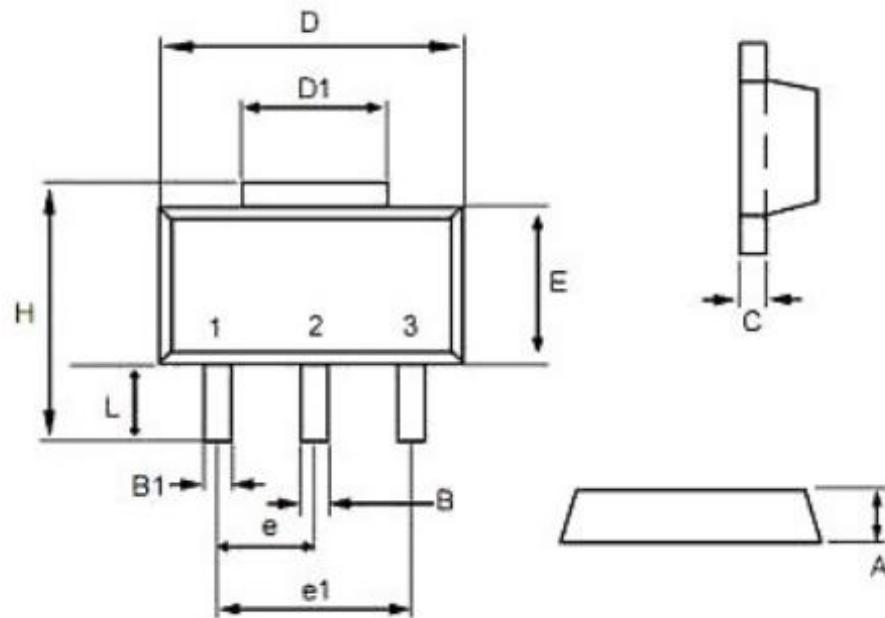
Characteristic 特性参数	Symbol 符号	Value 额定值	Unit 单位
Peak Repetitive Off-State Voltage 峰值可重复断态耐压	V <sub>DRM</sub> , V <sub>RRM</sub>	600	V
On-State RMS Current 通态均方根电流	I <sub>T(RMS)</sub>	1	A
On-State Average Current 通态平均电流	I <sub>T(AV)</sub>	1	A
Peak Non-Repetitive Surge Current @25°C 峰值不可重复浪涌电流	I <sub>TSM</sub>	10	A
Circuit Fusing Considerations(t=10ms) 电路保险指数	I <sup>2</sup> t	1.28	A <sup>2</sup> s
Peak Gate Current-Forward (Pulse Width ≤ 1 us) 正向门极峰值电流	I <sub>GM</sub>	2	A
Peak Gate Voltage-Reverse (Pulse Width ≤ 1 μs) 反向门极峰值电压	V <sub>GRM</sub>	5	V
Forward Peak Gate Power (Pulse Width ≤ 1 μs) 正向门极峰值功率	P <sub>GM</sub>	5	W
Forward Average Gate Power (t=8.3ms) 正向门极平均功率	P <sub>G(AV)</sub>	0.5	W
Critical rate of rise of on-state current 通态电流上升率	dI/dt	I II III IV	50 10 A/us
Thermal Resistance J-C 结到管壳热阻	R <sub>θJC</sub>	31	°C/W

## ■ Electrical Characteristics 电特性

(T<sub>A</sub>=25°C unless otherwise noted 如无特殊说明，温度为 25°C)

Characteristic Parameters 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位	Condition 条件
Peak Forward Blocking Current 峰值正向漏电流	I <sub>DRM</sub>	T <sub>c</sub> =25°C T <sub>c</sub> =125°C	5 500	μA	V <sub>D</sub> =V <sub>DRM</sub>
Peak Reverse Blocking Current 峰值反向漏电流	I <sub>RRM</sub>	T <sub>c</sub> =25°C T <sub>c</sub> =125°C	5 500	μA	V <sub>R</sub> =V <sub>RRM</sub>
Peak Forward On-State Voltage 峰值正向通态电压	V <sub>TM</sub>		1.7	V	I <sub>TM</sub> =1.4A
Gate Trigger Current 触发电流	I <sub>GT</sub>	I II III IV	5 10 20	mA	V <sub>D</sub> =12V R <sub>L</sub> =33Ω
Gate Trigger Voltage 触发电压	V <sub>GT</sub>		1.3	V	V <sub>D</sub> =12V R <sub>L</sub> =33Ω
Holding Current 维持电流(T/D)	I <sub>H</sub>		5/7	mA	I <sub>T</sub> =100mA
Latch Current 擎住电流(T/D)	I <sub>L</sub>	I III IV II	5/5 10/20	mA	I <sub>G</sub> =1.2I <sub>GT</sub>
Off-state Voltage Change 断态电压临界上升率(T/D)	dv/dt	20/50		V/μS	V <sub>D</sub> =2/3V <sub>DRM</sub>
Gate Non Trigger Voltage 门极不触发电压	V <sub>GD</sub>	0.2		V	V <sub>D</sub> =V <sub>DRM</sub>

## ■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047